

# 20V N-Channel MOSFET



TO-252

#### Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

#### PRODUCT SUMMARY

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)	
20	30 @ V <sub>GS</sub> = 10V	8	
	40 @ V <sub>GS</sub> = 4.5V	6	

## **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

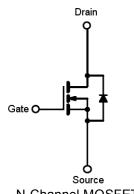
## **Application**

- Load Switch
- PA Switch

## **Ordering Information**

Part No.	Package	Packing	
TSM12N02CP RO	TO-252	T&R	

## **Block Diagram**



N-Channel MOSFET

## Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	20V	V
Gate-Source Voltage		$V_{GS}$	±12	V
Continuous Drain Current, V <sub>GS</sub> @4.5V	•	l <sub>D</sub>	12	А
Pulsed Drain Current, V <sub>GS</sub> @4.5V		I <sub>DM</sub>	30	Α
Continuous Source Current (Diode Co	nduction) <sup>a,b</sup>	I <sub>S</sub>	1.7	Α
Maximum Power Dissipation	Ta = 25 °C	Ъ	60	W
	Ta = 70 °C	P <sub>D</sub>	23	V V
Operating Junction Temperature		TJ	+150	°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## **Thermal Performance**

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	$T_L$	10	S
Junction to Case Thermal Resistance	$R\Theta_{JC}$	2.2	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖JA	50	°C/W

## Notes:

- a. Maximum DC current limited by the package
- b. Surface Mounted on 1" x 1" FR4 Board, t ≤ 10 sec.



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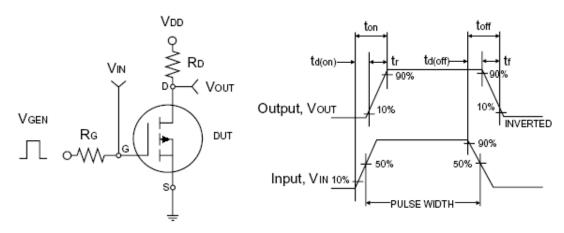


**Electrical Specifications** 

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV <sub>DSS</sub>	20		-	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	V <sub>GS(TH)</sub>	0.6		-	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I <sub>DSS</sub>			1.0	uA
On-State Drain Current	V <sub>DS</sub> ≥5V, V <sub>GS</sub> = 10V	I <sub>D(ON)</sub>	12			Α
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 6A$			30	40	mΩ
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 8A$	$R_{DS(ON)}$		21	30	
Forward Transconductance	$V_{DS} = 10V, I_D = 6A$	g <sub>fs</sub>	7	13	I	S
Diode Forward Voltage	$I_S = 1.7A$ , $V_{GS} = 0V$	V <sub>SD</sub>			1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	$V_{DS} = 10V, I_D = 6A$ $I_S = 1.7A, V_{GS} = 0V$ $V_{DS} = 10V, I_D = 6A,$ $V_{GS} = 4.5V$	$Q_g$		4.86	-	
Gate-Source Charge		$Q_gs$		0.92		nC
Gate-Drain Charge	- V <sub>GS</sub> = 4.5V	$Q_{gd}$		1.4		
Input Capacitance	., ., .,	C <sub>iss</sub>		562		
Output Capacitance	$V_{DS} = 8V, V_{GS} = 0V,$ f = 1.0MHz	C <sub>oss</sub>		106		pF
Reverse Transfer Capacitance	1 - 1.0101112	C <sub>rss</sub>		75		
Switching <sup>c</sup>						
Turn-On Delay Time		t <sub>d(on)</sub>		8.1		
Turn-On Rise Time	$V_{DD} = 10V, I_{D} = 1A,$ $V_{GEN} = 10V,$ $R_{G} = 16Ω$	t <sub>r</sub>		9.95		nC
Turn-Off Delay Time		t <sub>d(off)</sub>		21.85		nS
Turn-Off Fall Time	1012	t <sub>f</sub>		5.35		

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

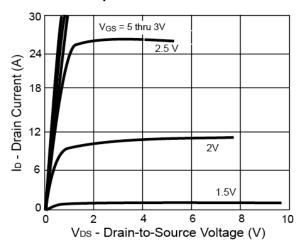


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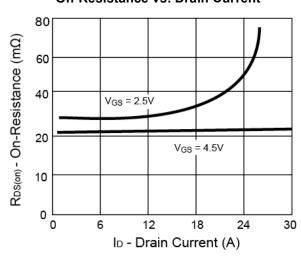


## **Electrical Characteristics Curve** (Ta = 25 °C, unless otherwise noted)

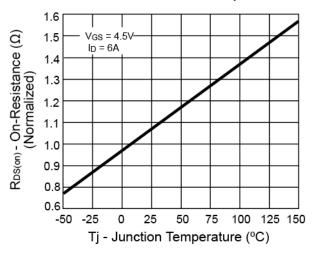
#### **Output Characteristics**



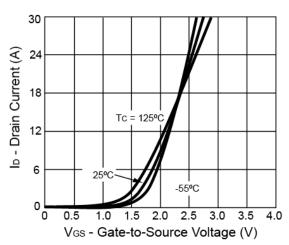
#### **On-Resistance vs. Drain Current**



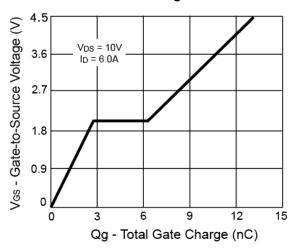
#### On-Resistance vs. Junction Temperature



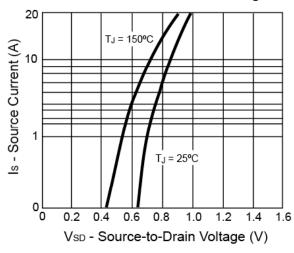
#### **Transfer Characteristics**



#### **Gate Charge**



#### Source-Drain Diode Forward Voltage





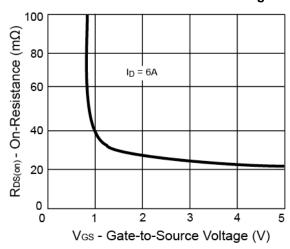
100 125 150

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#### Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage



# Threshold Voltage 0.6 0.4 0.2 0.2 0.0 -0.0 -0.0 -0.0 -0.0 -0.1

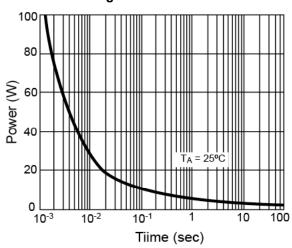
25

50

Tj - Junction Temperature (°C)

75

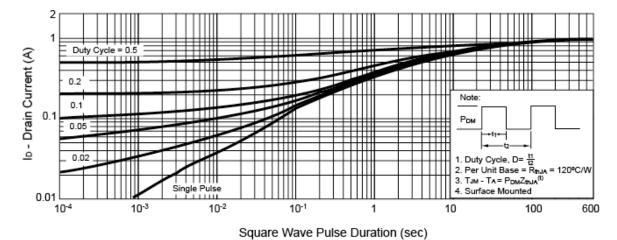
**Single Pulse Power** 



#### Normalized Thermal Transient Impedance, Junction-to-Ambient

-0.6

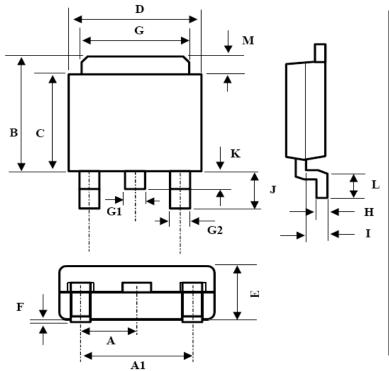
-50 -25







# **SOT-252 Mechanical Drawing**



	TO-252 DIMENSION					
DIM	MILLIMETERS		INCHES			
DIIVI	MIN	MAX	MIN	MAX		
Α	2.3E	BSC	0.09BSC			
A1	4.6BSC		0.18	BSC		
В	6.80	7.20	0.268	0.283		
С	5.40	5.60	0.213	0.220		
D	6.40	6.65	0.252	0.262		
Е	2.20	2.40	0.087	0.094		
F	0.00	0.20	0.000	0.008		
G	5.20	5.40	0.205	0.213		
G1	0.75	0.85	0.030	0.033		
G2	0.55	0.65	0.022	0.026		
Н	0.35	0.65	0.014	0.026		
	0.90	1.50	0.035	0.059		
J	2.20	2.80	0.087	0.110		
K	0.50	1.10	0.020	0.043		
L	0.90	1.50	0.035	0.059		
М	1.30	1.70	0.051	0.67		



# TSM12N02 20V N-Channel MOSFET

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